DISCRETE SEMICONDUCTORS

DATA SHEET

PDTA123J series PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

Product data sheet Supersedes data of 2003 Apr 14 2004 Aug 02



PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

PDTA123J series

FEATURES

- Built-in bias resistors
- · Simplified circuit design
- Reduction of component count
- · Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- · Inverter and interface circuits
- Circuit driver.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V_{CEO}	collector-emitter voltage	_	-50	V
Io	output current (DC)	_	-100	mA
R1	bias resistor	2.2	_	kΩ
R2	bias resistor	47	_	kΩ

DESCRIPTION

PNP resistor-equipped transistor (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PAC	KAGE	MARKING CODE	NPN COMPLEMENT	
ITPE NUMBER	PHILIPS	EIAJ	MARKING CODE	NPN COMPLEMENT	
PDTA123JE	SOT416	SC-75	27	PDTC123JE	
PDTA123JEF	SOT490	SC-89	27	PDTC123JEF	
PDTA123JK	SOT346	SC-59	43	PDTC123JK	
PDTA123JM	SOT883	SC-101	DG	PDTC123JM	
PDTA123JS	SOT54 (TO-92)	SC-43	TA123J	PDTC123JS	
PDTA123JT	SOT23	-	*23 ⁽¹⁾	PDTC123JT	
PDTA123JU	SOT323	SC-70	*43 ⁽¹⁾	PDTC123JU	

Note

- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

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SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TVDE NUMBER	CIMPLIFIED OUTLINE AND CYMPOL		PINNING
TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PIN	DESCRIPTION
PDTA123JS	1 R1 R2 3 MAM338	1 2 3	base collector emitter
PDTA123JE PDTA123JEF PDTA123JK PDTA123JT PDTA123JU	3 1 R1 1 R2 1 DD 2 Top view	1 2 3	base emitter collector
PDTA123JM	2 R1 3 Bottom view ADB267	1 2 3	base emitter collector

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-50	V
V _{CEO}	collector-emitter voltage	open base	_	-50	V
V _{EBO}	emitter-base voltage	open collector	_	-10	V
VI	input voltage				
	positive		_	+5	V
	negative		_	-12	V
Io	output current (DC)		_	-100	mA
I _{CM}	peak collector current		_	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT54	note 1	_	500	mW
	SOT23	note 1	_	250	mW
	SOT346	note 1	_	250	mW
	SOT323	note 1	_	200	mW
	SOT416	note 1	_	150	mW
	SOT490	notes 1 and 2	_	250	mW
	SOT883	notes 2 and 3	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μ m copper strip line.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	in free air		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT416	note 1	833	K/W
	SOT490	notes 1 and 2	500	K/W
	SOT883	notes 2 and 3	500	K/W

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μ m copper strip line.

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PDTA123J series

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0$	_	_	-100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0$	_	_	-1	μΑ
		$V_{CE} = -30 \text{ V}; I_B = 0; T_j = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	_	-180	μΑ
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}$	100	_	_	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -5 \text{ mA}; I_B = -0.25 \text{ mA}$	_	_	-100	mV
$V_{i(off)}$	input-off voltage	$I_C = -100 \mu A; V_{CE} = -5 V$	_	-0.6	-0.5	V
$V_{i(on)}$	input-on voltage	$I_C = -5 \text{ mA}; V_{CE} = -0.3 \text{ V}$	-1.1	-0.75	_	V
R1	input resistor		1.54	2.2	2.86	kΩ
<u>R2</u> R1	resistor ratio		17	21	26	
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = -10 \text{ V}$; $f = 1 \text{ MHz}$	_	_	3	pF

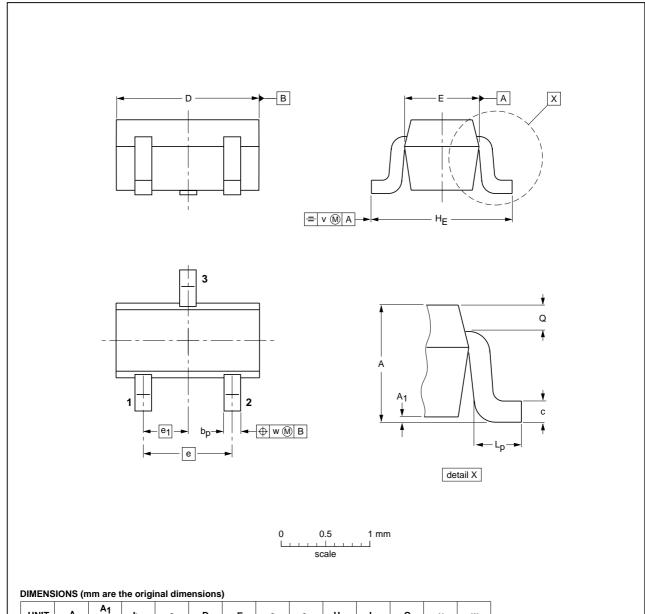
PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

PDTA123J series

PACKAGE OUTLINES



SOT416



UNIT	Α	A ₁ max	bp	С	D	E	e	e ₁	HE	Lp	Q	٧	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

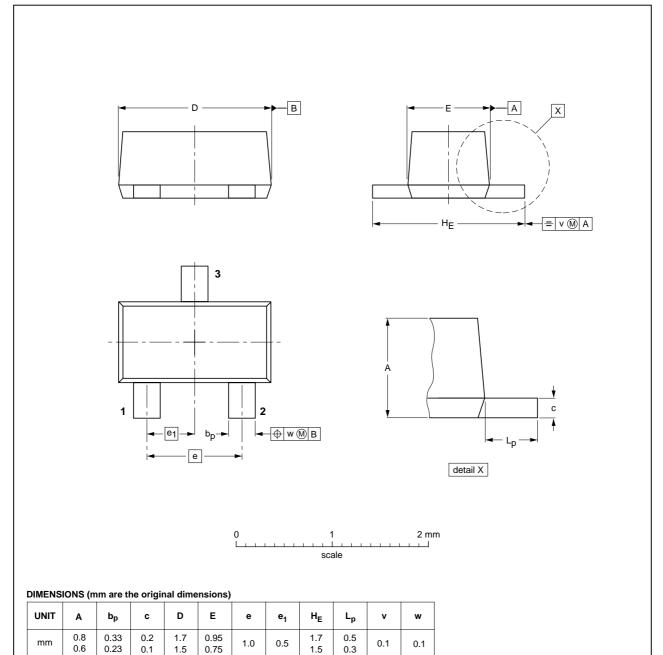
OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT416			SC-75		04-11-04 06-03-16	

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

PDTA123J series

Plastic surface-mounted package; 3 leads

SOT490



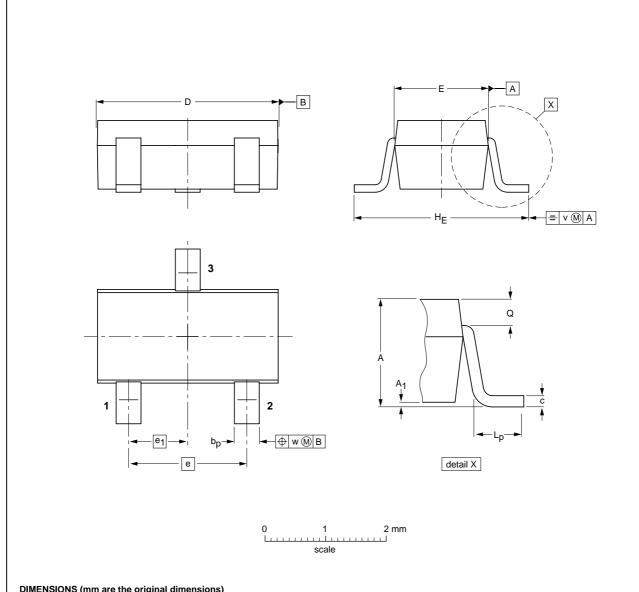
OUTLINE		REFER	ENCES		EUROPEAN	ISSUE DATE	
VERSION	IEC JEDEC JEITA		JEDEC JEITA		PROJECTION	ISSUE DATE	
SOT490			SC-89			05-07-28 06-03-16	

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

PDTA123J series

Plastic surface-mounted package; 3 leads

SOT346



DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁	bp	С	D	E	е	e ₁	HE	Lp	Q	v	w
mm	1.3 1.0	0.1 0.013	0.50 0.35	0.26 0.10	3.1 2.7	1.7 1.3	1.9	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2

OUTLINE		EUROPEAN	ICCUIT DATE			
VERSION IEC		JEDEC JEITA		PROJECTION	ISSUE DATE	
SOT346		TO-236	SC-59A		-04-11-11 06-03-16	

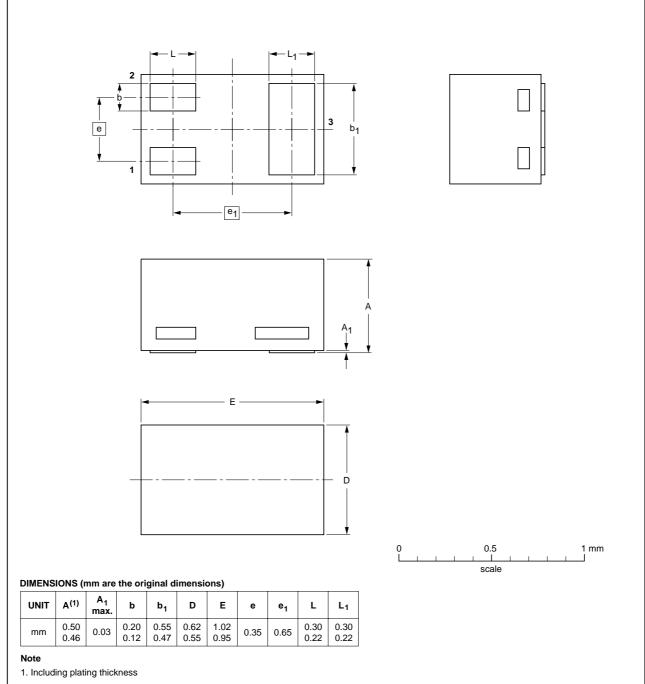
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PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

PDTA123J series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



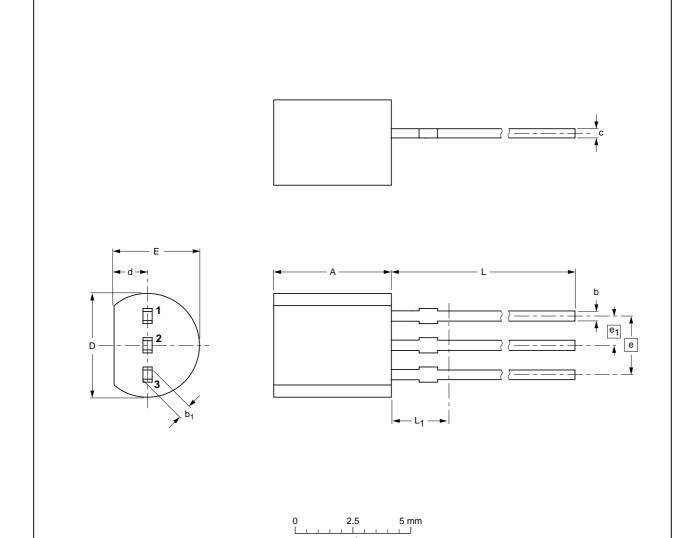
OUTLINE		REFER	RENCES	EUROPEAN		
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT883			SC-101		03-02-05 03-04-03	

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

PDTA123J series

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



DIMENSIONS (mm are the original dimensions)

UNIT	Α	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾ max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

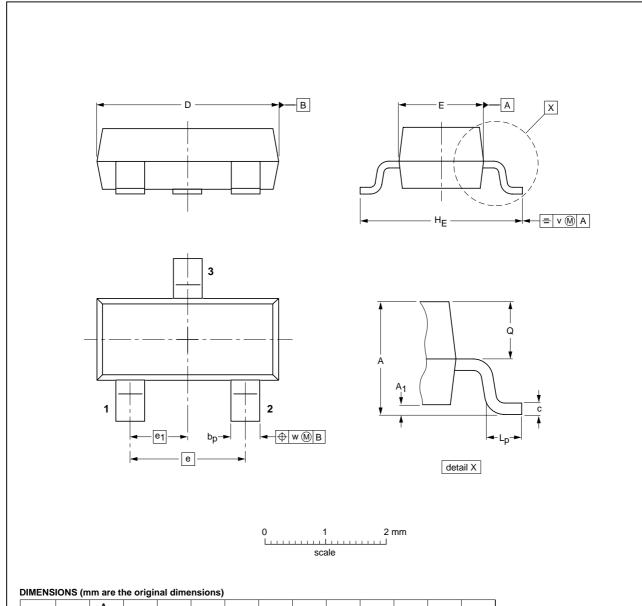
OUTLINE		REFER	ENCES		ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT54		TO-92	SC-43A			-04-06-28- 04-11-16	

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

PDTA123J series

Plastic surface-mounted package; 3 leads

SOT23



UNIT	Α	A ₁ max.	bp	С	D	E	е	e ₁	HE	Lp	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

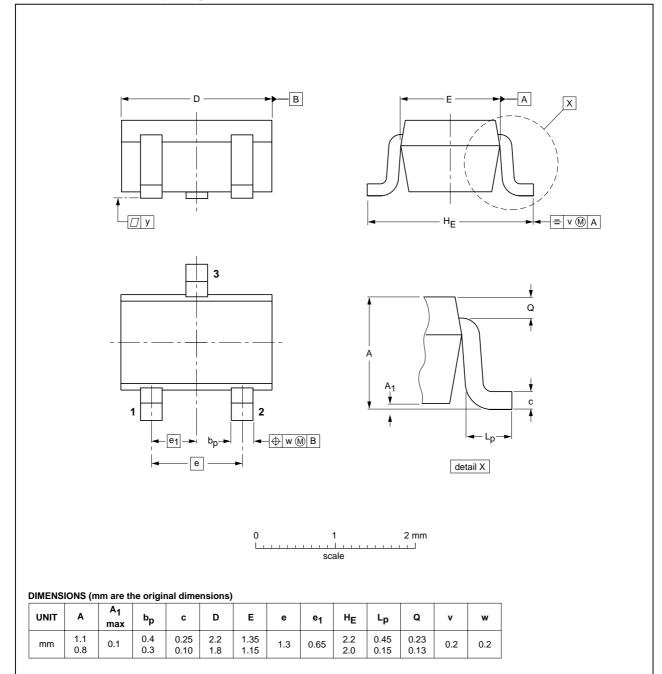
OUTLINE		REFER	ENCES	CES EUROPEAN			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT23		TO-236AB				-04-11-04- 06-03-16	

PNP resistor-equipped transistors; $R1 = 2.2 \text{ k}\Omega$, $R2 = 47 \text{ k}\Omega$

PDTA123J series

Plastic surface-mounted package; 3 leads

SOT323



OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	1330E DATE
SOT323			SC-70		-04-11-04 06-03-16

REFERENCES

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PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

PDTA123J series

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Contact information

For additional information please visit: http://www.nxp.com
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